

TECHNICAL DATA
DATA SHEET 1178, REV -

THREE PHASE FULL WAVE BRIDGE RECTIFIER ASSEMBLY

DESCRIPTION: A 50/100/150 VOLT, 9.0 AMP, 30 NANOSECOND THREE PHASE BRIDGE RECTIFIER ASSEMBLY.

MAX. RATINGS / ELECTRICAL CHARACTERISTICS All ratings are at $T_A = 25^{\circ}\text{C}$ unless otherwise specified.

RATING	CONDITIONS	MIN	TYP	MAX	UNIT
Peak Inverse Voltage (PIV)	-	-	-	50 100 150	Vdc
Average DC Output Current ($T_C = \text{Case Temp}$) (I_o)	$T_C = 55^{\circ}\text{C}$ $T_C = 100^{\circ}\text{C}$ $T_C = 125^{\circ}\text{C}$	-	-	9.0 6.5 4.0	Amps
Average DC Output Current Ambient Temp. (no heat sink) (I_o)	$T_A = 25^{\circ}\text{C}$ $T_A = 55^{\circ}\text{C}$ $T_A = 100^{\circ}\text{C}$	-	-	2.5 2.0 1.3	Amps
Peak Single Cycle Surge Current (I_{FSM})	$t_p = 8.3 \text{ ms}$ Single Half Cycle Sine Wave, Superimposed On Rated Load	-	-	60	Amps(pk)
Peak Recurring Surge Current (I_{FRM})	$T_A = 25^{\circ}\text{C}$	-	-	17.5	Amps
Operating and Storage Temp. (T_{op} & T_{stg})	-	-55	-	+150	$^{\circ}\text{C}$
Maximum Forward Voltage (V_f)	$I_f = 3.0\text{A}$ (300 μsec pulse, duty cycle < 2%)	-	-	1.2	Volts
Maximum Instantaneous Reverse Current At Rated (PIV)	$T_A = 25^{\circ}\text{C}$ $T_A = 100^{\circ}\text{C}$	-	-	5.0 100	μAmps
Reverse Recovery Time (t_{rr})	$I_f = 0.5\text{A}$, $I_r = 1.0\text{A}$, $I_{rr} = 0.25\text{A}$	-	-	30	nsec
Thermal Resistance (θ_{JL})	-	-	-	4.0	$^{\circ}\text{C/W}$

MECHANICAL DIMENSIONS: In Inches / mm

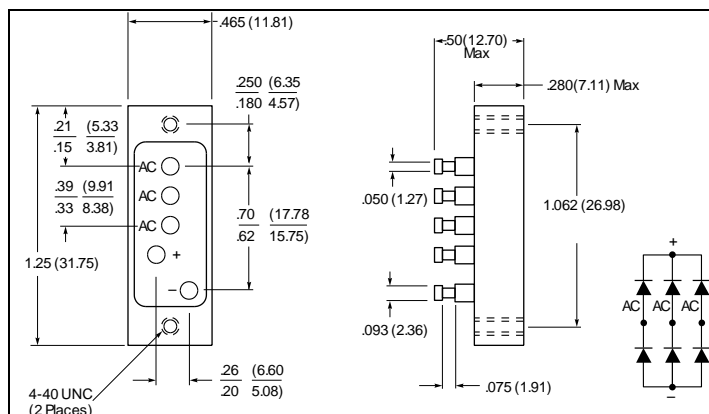


FIG. 409

Note: Case finish - Black Anodized

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